--CROSS REFERENCE TO RELATED U.S. APPLICATIONS

This is a divisional application of application Serial No. 09/920,713, filed August 3, 2001, which is a divisional of Serial No. 09/580,624, now U.S. Patent No. 6,281,111, filed May 30, 2000, which is a divisional of Serial No. 08/959,667, now U.S. Patent No. 6,097,091, filed October 29, 1997, which are hereby incorporated by reference in their entirety for all purposes.--

In The Claims:

Please cancel claims 1-21 without prejudice or disclaimer of the subject matter therein.

Please add claims 22-31 as follows:

--22. A semiconductor apparatus comprising:

a semiconductor substrate having a main surface which includes a semiconductor integrated circuit;

a base member which is formed on the main surface of the semiconductor substrate, the base member being formed of a first resin and having a first surface and a second surface opposite the first surface;

a conductive layer having a first portion arranged on the main surface of the semiconductor substrate and connected to the semiconductor integrated circuit, a middle portion extending from the first portion, and a second portion which extends

from the middle portion and is arranged on the second surface of the base member; and

a second resin which is formed on the first and middle portions of the conductive layer so that the first portion of the conductive layer is arranged between the main surface of the semiconductor substrate and the second resin, and so that the middle portion of the conductive layer is arranged between the base member and the second resin.

23. The semiconductor apparatus according to claim 22, wherein the conductive layer and the base member constitute an electrode.

24. The semiconductor apparatus according to claim 22, wherein the first and second resins are a same material and have a same thermal expansion coefficient.

25. The semiconductor apparatus according to claim 22, wherein the second portion of the conductive layer has a surface exposed from the second resin.

26. The semiconductor apparatus according to claim 22, further comprising:

a connection substrate arranged to face the main surface of the semiconductor substrate and which is connected to the second portion of the conductive layer,

the second portion of the conductive layer being arranged between the second

surface of the base member and the connection substrate.

27. The semiconductor apparatus according to claim 26, wherein the semiconductor substrate is mounted on the connection substrate by a face-down technique.

28. A semiconductor apparatus comprising:

a semiconductor substrate having an integrated circuit on a main surface;

a base member of an insulative material formed on the main surface of the semiconductor substrate;

a conductive layer formed on the main surface of the semiconductor substrate, the conductive layer being connected to the integrated circuit and having an extended portion that extends onto a top surface of the base member; and

a sealing member formed on the main surface of the semiconductor substrate, the conductive layer and side surfaces of the base member, wherein the extended portion of the conductive layer is exposed from the sealing member.

29. The semiconductor apparatus of claim 28, wherein the base member and the sealing member are a same material.

30. The semiconductor apparatus of claim 29, wherein the base member and the

sealing member are a polymide resin.

31. The semiconductor apparatus of claim 28, further comprising a connection substrate facing the main surface of the semiconductor substrate and being connected to the extended portion of the conductive layer exposed from the sealing member.--